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### **EUROPEAN PATENT APPLICATION**

(21) Application number: 92305309.4

② Date of filing: 10.06.92

(a) Int. Cl.5: **C23C** 16/26, C04B 41/88, B23B 27/20, C22C 1/10

Priority: 10.06.91 GB 9112408

43 Date of publication of application: 16.12.92 Bulletin 92/51

Designated Contracting States:
AT BE CH DE FR GB IT LI NL SE

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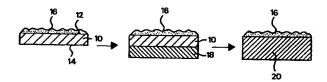
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## Tool components.

A method is provided for producing a tool component which comprises a CVD diamond layer (16) bonded to a cemented carbide substrate (20). The method includes the steps of providing a mass of carbide particles bonded into a layer (10) with an organic binder, removing the organic binder to produce a porous mass of the particles, depositing a

layer (16) of diamond by CVD on a surface (12) of the porous mass, placing the porous mass in contact with a layer (18) of binder metal particles bonded with an organic binder, and heating the product to allow the metal binder particles to melt and infiltrate the carbide particles and produce a cemented carbide substrate (20) for the CVD diamond layer (16).

METHOD 1



METHOD 2

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#### **BACKGROUND OF THE INVENTION**

This inv ntion r lates to tool compon nts.

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It has been proposed in the literature to produce tool components by depositing a layer of diamond by chemical vapour deposition (CVD) on a surface of a cemented carbide substrate. One of the difficulties which such a method gives rise to is the achievement of a strong bond between the CVD diamond layer and the substrate.

Chemical vapour deposition of diamond involves the synthesis of diamond from the gas phase. The process generally involves providing a mixture of hydrogen or oxygen gas and a suitable gaseous carbon compound such as a hydrocarbon, applying sufficient energy to that gas to dissociate the hydrogen or oxygen into atomic hydrogen or oxygen and the gas into active carbon ions, atoms or CH radicals, and allowing such active species to disposit as diamond on a substrate. Dissociation of the gases can take place by a variety of methods. These methods include the use of a hot filament, a plasma assisted method using microwave, RE or DC plasma, or the use of a plasma jet.

According to the present invention, there is provided a method of producing a tool component comprising a CVD diamond layer bonded to a cemented carbide substrate which comprises a mass of carbide particles and a metal binder, the method including the steps of:

- (i) providing a porous, bonded mass of carbide particles;
- (ii) depositing a layer of diamond by CVD on a surface of the porous mass;
- (iii) placing the porous mass in contact with a mass of the binder metal; and
- (iv) heating the product of step (iii) to an elevated temperature to allow the metal binder particles to melt and infiltrate the carbide particles and produce a cemented carbide substrate for the CVD diamond layer.

The tool insert which is produced by the method of the invention comprises a CVD diamond lay r bonded to a cemented carbide substrate. In the method, the cemented carbide substrate is produced in situ and this, it has been found, allows for an excellent bond between the carbide and the CVD diamond to be produced.

Preferably, the porous, bonded mass of carbid particles is produced by providing a mass of carbide particles in bonded form with an organic binder and then removing the organic binder.

The mass of the binder metal in step (iii) may be in particulat or shim form. Wh n it is in particulat form, it is pr f rably provided in bond d form with an organic binder which is removed prior to st p (iv). The r sulting mass will also be a porous mass.

The organic bind r will typically be a highly viscous organic bonding agent which will volatilise at a temperatur of about 350°C or high r. An xampl of such a bonding agent is a c llulos ether. Generally, such organic binders will be removed by heating the bonded layer to a temperature in the range of 475 to 700°C. Such heating can be achieved by any of the variety of methods such as low pressure hydrogen plasma, inductive vacuum heating or the like.

The heating in step (iv) will be such as to cause the metal binder particles to melt. Generally, temperatures in excess of 1000°C will be required and under such conditions the heating should take place in a vacuum or a non-oxidising atmosphere to avoid damage occurring to the CVD diamond layer. Typically, the elevated temperature required to cause the binder metal to infiltrate the carbide particles will be maintained for a period of 10 to 40 minutes.

The cemented carbide may be any known in the art. Typically, the carbide particles will be tungsten, titanium, tantalum or chromium carbide particles and the binder metal will be nickel, cobalt or iron or alloys containing one or more of these metals.

The invention will be further described by way of example with reference to the drawings which illustrate schematically the steps involved in two embodiments of the invention.

Two embodiments of the invention will now be described with reference to the accompanying drawings. Referring first to method 1, a carbide particle based paper 10 is pre-cut to a desired shape. The paper has major surfaces 12 and 14 on opposite sides thereof. The paper comprises a mass of carbide particles such as tungsten carbide or chromium carbide held in a coherent form by an organic binder. The organic binder will typically be a highly viscous organic bonding agent which will volatilise at a temperature of about 350 °C or higher.

The carbide paper 10 is heated to a temperature in the range 475 to 700°C to cause the organic binder to volatilise, leaving a layer which is porous.

A layer 16 of CVD diamond is then deposited on the major surface 12. This layer may be deposited by any of the known CVD methods. Such deposition will take place at a temperature in the range 600 to 800 °C in a vacuum.

Thereafter, the composite 10, 16 is placed on a layer 18 consisting of a mass of binder metal particles bonded with an organic bind r of th type described abov. The unbond diassembly is then subjected to an elevated temperature, gin rally higher than 1100°C, in a vacuum or non-oxidising atmosphir for a period of time to allow the bind r

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metal to melt, the organic bind r to volatilise and the binder m tal to infiltrate the carbide particles and form a c m nted carbid. The resulting product is a tool component comprising a CVD diamond layer 16 bonded to a cemented carbide substrate 20.

By way of example, the organic binder in the carbide based paper 10 may be volatilised by low pressure hydrogen plasma using the following conditions:

Hydrogen flow - 80 sccm

Pressure - 26 X102 to 80 X102 Pa

Power - 350 W

Time - 10 to 45 minutes

Temperature of carbide paper - 470 to 690°C

The diamond layer 16 may be deposited on the surface 12 by plasma chemical vapour deposition using the following conditions:

Hydrogen flow - 80 sccm

Methane flow - 0.85 sccm

Pressure - 65 X10<sup>2</sup> Pa

Temperature of carbide paper - 740 ° C

Diamond deposition rate - about 0,3 microns per hour

A second embodiment of the invention is illustrated by method 2 of the accompanying drawings. Referring to this method, a carbide paper 30 and metal binder paper 32, both as described above, are placed one on top of the other. The organic binder of the layers is caused to volatilise using the conditions described for the first embodiment leaving porous masses of the carbide particles and metal binder, respectively. A layer of CVD diamond 34 is then deposited on the surface 36 of the carbide paper 30. Thereafter, and while still under a nonoxidising atmosphere or a vacuum, the temperature is raised to the melting temperature of the binder metal to allow the binder metal to infiltrate the carbide particles and form a cemented carbide. The resulting product is again a tool component comprising a CVD diamond layer 34 bonded to a cemented carbide substrate 38.

The CVD diamond layer will typically have a thickness greater than 5 microns and preferably in the range 5 to 50 microns.

The carbide and binder metal papers may also include other particulate materials such as diamond or cubic boron nitride particles. When such other particulate materials are included they will typically be present in an amount of 5 to 50% by volume and have a particle size about the same as that of the carbide particles.

The tool components of the invention may be used as cutting tool inserts with the c m nted carbid substrat providing a readily brazeable surface. Alt rnatively, a surface of the carbide substrate can be metallised and this m tallised surfacused to bond the insert to a steel, carbid or lik

post. The tool components may also be used as wear parts.

#### **Claims**

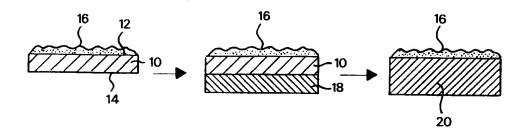
- A method of producing a tool component comprising a CVD diamond layer (16) bonded to a cemented carbide substrate (20) which comprises a mass of carbide particles and a metal binder, the method including the steps of:
  - (i) providing a porous, bonded mass (10) of carbide particles;
  - (ii) depositing a layer (16) of diamond by CVD on a surface (12) of the porous mass;
  - (iii) placing the porous mass (10) in contact with a mass (18) of the binder metal; and
  - (iv) heating the product of step (iii) to an elevated temperature to allow the metal binder particles to melt and infiltrate the carbide particles and produce a cemented carbide substrate (20) for the CVD diamond layer (16).
- 2. A method according to claim 1 wherein the porous, bonded mass (10) of carbide particles is produced by providing a mass of carbide particles in bonded form (10) with an organic binder and removing the organic binder.
- 30 3. A method according to claim 1 or claim 2 wherein the mass of the binder metal in step (iii), is in particulate, bonded form (18) with an organic binder which is removed prior to the heating of step (iv).
  - 4. A method according to claim 2 or claim 3 wherein the organic binder volatilises at a temperature of about 350°C or higher and this binder is removed by heating the bonded form to a temperature in the range of 475 to 700°C.
  - 5. A method according to any one of the preceding claims wherein the porous, bonded mass (10) of carbide particles is in the form of a layer having major surfaces (12, 14) on each of opposite sides thereof and the CVD diamond (16) is deposited on one of these surfaces (12).
- 50 6. A method according to any one of the preceding claims wherein the carbide particles are selected from tungsten, tantalum, titanium and chromium carbide particles.
  - A m thod according to any on of th prec ding claims wherein the m tal binder is selected from nick I, cobalt, iron and alloys containing on or mor of th s m tals.

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8. A method according to any on of th pr c ding claims wh rein the elevated temperature in st p (iv) is maintained for a period of 10 to 40 minut s.

9. A tool component made using a method according to any preceding claim.

# METHOD 1



## METHOD 2

